

## ABSTRACT:

The semiconductor device comprises a substrate (10) with a first (1) and an opposed second side (2), at which first side a plurality of transistors and interconnects is present, which are covered by a protective security covering (16), which device is further provided with bond pad regions (14). The protective security covering (16) comprises a  
5 substantially non-transparent and substantially chemically inert security coating (16), and the bond pad regions (14) are accessible from the second side of the substrate (10). The semiconductor device can be suitable made with a substrate transfer technique, in which a second substrate (24) is provided at the protective security covering (16).

10 Fig. 6